

ABSTRACT

The present disclosure provides a semiconductor structure and a method for manufacturing the same. The semiconductor structure at least includes: an underlying conductive layer and a blocking portion, a plane in which the blocking portion is located being
5 located above a plane in which the underlying conductive layer is located, and projections of the blocking portion and the underlying conductive layer in the vertical direction having an overlapping region; a three-dimensional structure, the three-dimensional structure including a first portion and a second portion, a top surface of the blocking portion being higher than a bottom surface of the second portion and being lower than or flush with a bottom surface of
10 the first portion, and at least a part of the first portion being located directly above the overlapping region; a contact hole and a first conductive layer, a plane in which the first conductive layer is located being higher than a top surface of the three-dimensional structure, the contact hole being directly connected to the first conductive layer, the underlying conductive layer being electrically connected to the first conductive layer through the contact
15 hole, and the contact hole being located on a side of the first portion away from the second portion; and a first isolation layer, the first isolation layer being configured to fill a region between the contact hole and the three-dimensional structure and a region between different contact holes.

[FIG. 1]